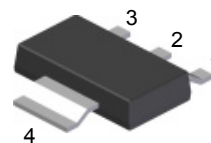


Features

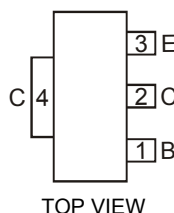
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DZT491)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 3)**



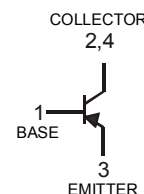
SOT-223

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish - Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)



TOP VIEW



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-80	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Continuous Current (Note 3)	I _C	-1	A
Peak Collector Current	I _{CM}	-2	A
Base Current	I _B	-200	mA
Power Dissipation (Note 3)	P _d	1	W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Cutoff Current	I _{CBO}	—	—	-100	nA	V _{CB} = -60V
Emitter-Base Cutoff Current	I _{EBO}	—	—	-100	nA	V _{EB} = -4V
Collector-Emitter Cutoff Current	I _{CES}	—	—	-100	nA	V _{CES} = -60V
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-80	—	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-60	—	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	—	—	V	I _E = 100μA
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	—	-0.3	V	I _C = -500mA, I _B = -50mA
		—	—	-0.6	V	I _C = -1A, I _B = -100mA
		100	—	—	—	V _{CE} = -5V, I _C = -1mA
		100	—	300	—	V _{CE} = -5V, I _C = -500mA
		80	—	—	—	V _{CE} = -5V, I _C = -1A
DC Current Gain	h _{FE}	15	—	—	—	V _{CE} = -5V, I _C = -2A
		—	—	-1.2	V	I _C = -1A, I _B = -100mA
		—	—	-1	V	I _C = -1A, V _{CE} = -5V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	—	-1.2	V	I _C = -1A, I _B = -100mA
Base-Emitter Turn-On Voltage	V _{BE(on)}	—	—	-1	V	I _C = -1A, V _{CE} = -5V
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f _T	150	—	—	MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz
Output Capacitance	C _{obo}	—	13	—	pF	V _{CB} = -10V, f = 1MHz

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 4. Measured under pulsed conditions. Pulse width = 300ms. Duty cycle ≤ 2%.

Typical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

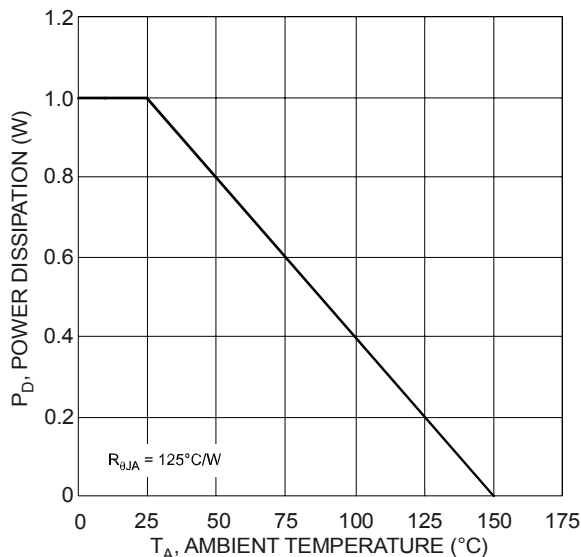


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

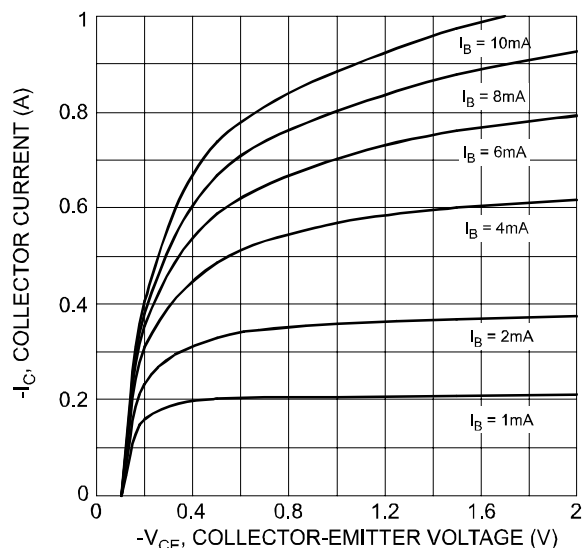


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

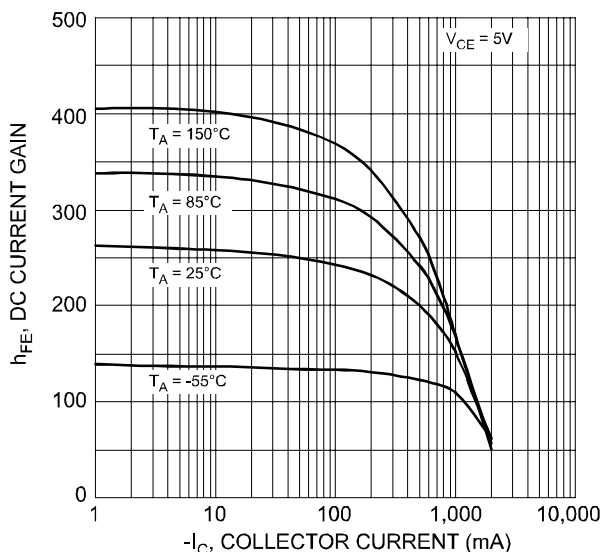


Fig. 3 Typical DC Current Gain vs. Collector Current

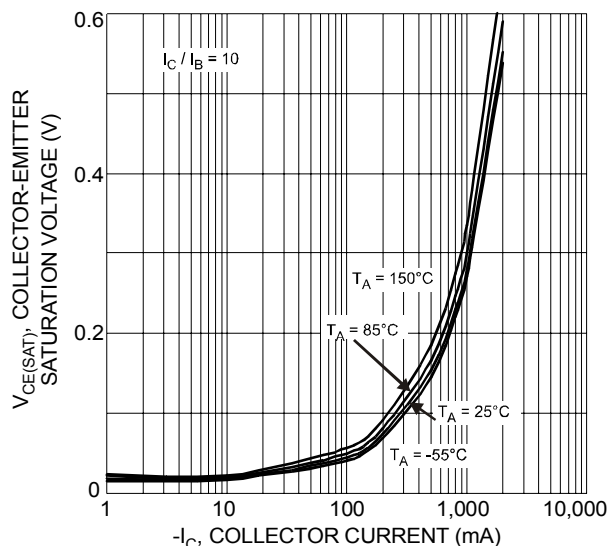


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

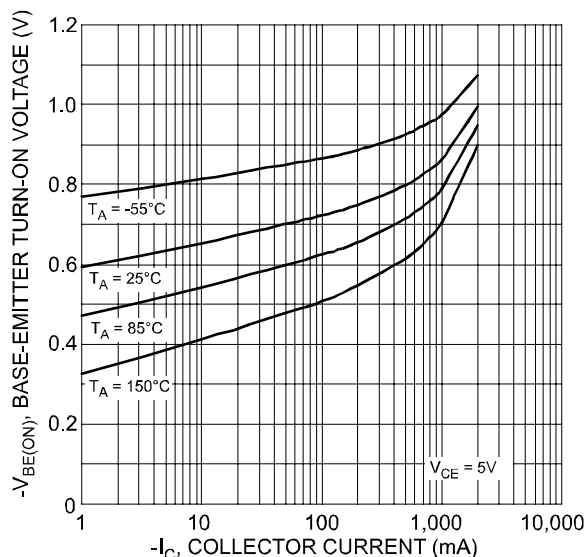


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

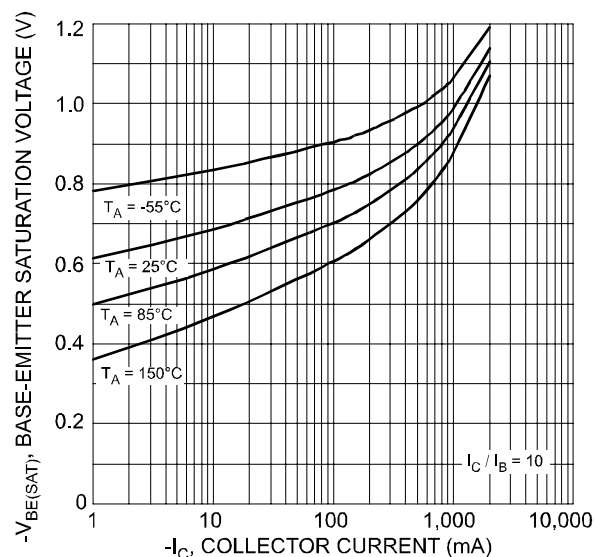
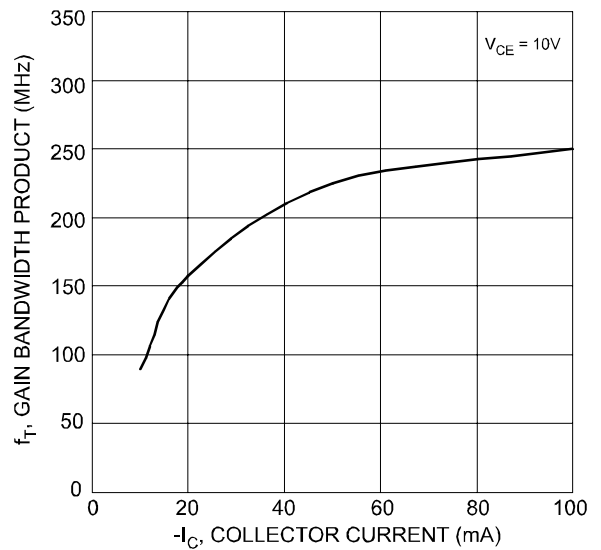
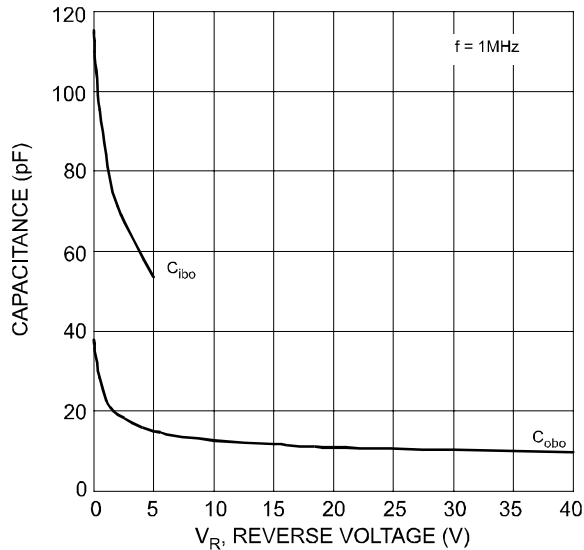


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

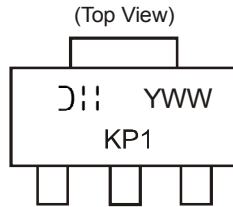


Ordering Information (Note 5)

Device	Packaging	Shipping
DZT591C-13	SOT-223	2500/Tape & Reel

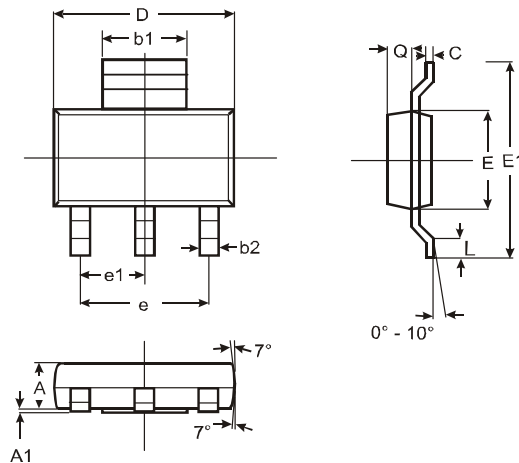
Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

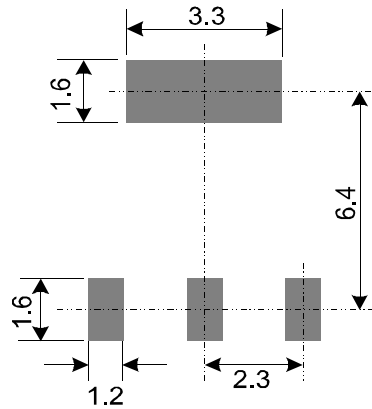


D = Manufacturer's code marking
 KP1 = Product type marking code
 YWW = Date code marking
 Y = Last digit of year ex: 7 = 2007
 WW = Week code 01 - 52

Package Outline Dimensions



SOT-223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b1	2.90	3.10	3.00
b2	0.60	0.80	0.70
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	—	—	4.60
e1	—	—	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout: (Based on IPC-SM-782)

(Unit: mm)

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